

ABSTRACT

The present invention relates to a method for preparing a SiC-Si₃N₄ composite material and a SiC-Si₃N₄ composite material prepared according to same and comprises the steps of: preparing a mold; and forming a SiC-Si₃N₄ composite material by introducing, to
5 the mold, a source gas comprising Si, N and C, at 1100 to 1600°C. More particularly, the present invention provides the SiC-Si₃N₄ composite material of high purity that is applicable to a semiconductor process, and increases the thermal shock strength of a SiC material by causing Si₃N₄, which is a material with a high thermal shock strength, to grow together via a CVD method.

10 FIG. 3